Product Change Notification

Product Group: SIL/Thursday August 6, 2026/PCN-SIL-000505-2026-REV-0

Additional Wafer Fabrication Capacity for Vishay Siliconix ICs for SIC645xx

For further information, please contact your regional Vishay office.

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Description of Change: Vishay Siliconix has expanded MOSFET production capacity by qualifying Vanguard International Semiconductor, Fab 3 in Taiwan as an additional foundry supplier.

Reason for Change: The additional MOSFET fabrication location has been qualified to increase manufacturing capacity and to provide an alternate geographic location for production.

Expected Influence on Quality/Reliability/Performance: There will be no negative effect on performance, quality or reliability.

Part Numbers/Series/Families Affected: SIC645ADR-T1-GE3, SIC645AER-T1-GE3, SIC645ALR-T1-GE3, SIC645ER-T1-GE3,

Vishay Brand(S): Vishay Siliconix

Time Schedule:

Start Shipment Date: Thursday October 15, 2026

Sample Availability: Samples will be available starting September 1, 2026

Product Identification: Lot number

Qualification Data: Please see attached.

This PCN is considered approved, without further notification, unless we receive specific customer concerns before Thursday October 1, 2026 or as specified by contract.

Issued By: Lisette Saba, malinalisette.saba@vishay.com

Qualification Data

July 2026

Reliability Test Result

EVAL	STRESS	STEP	TEST CONDITION	HR-CYC	S S	FAIL	DONE	TEST TYPE	FAIL CODE
2660062	DYN OP LIF	0	DYN OP LF (12	0	82	0	X	ET	
		1	DYN OP LF (12	168	82	0	X	ET	
	ESD - C D	0	ESD' - C D MO	0	28	0	X	ET	
		1	ESD' - C D MO	125	3	0	X	ET	
		2	ESD' - C D MO	250	3	0	X	ET	
		3	ESD' - C D MO	500	3	0	X	ET	
		4	ESD' - C D MO	750	3	0	X	ET	
		5	ESD' - C D MO	1000	3	0	X	ET	
		6	ESD' - C D MO	1500	3	0	X	ET	
		7	ESD' - C D MO	2000	10	0	X	ET	
	ESD - H B	0	ESD' - H B MO	0	27	0	X	ET	
		1	ESD' - H B MO	125	3	0	X	ET	
		2	ESD' - H B MO	500	3	0	X	ET	
		3	ESD' - H B MO	1000	3	0	X	ET	
		4	ESD' - H B MO	1500	3	0	X	ET	
		5	ESD' - H B MO	2000	3	0	X	ET	
		6	ESD' - H B MO	2500	3	0	X	ET	
		7	ESD' - H B MO	3000	3	0	X	ET	
		8	ESD' - H B MO	3500	3	0	X	ET	
		9	ESD' - H B MO	4000	3	0	X	ET	
	LATCH-UP	0	LATCH-UP	0	36	0	X	ET	
		1	LATCH-UP	100	6	0	X	ET	
		2	LATCH-UP	150	6	0	X	ET	
		3	LATCH-UP	200	6	0	X	ET	
		4	LATCH-UP	300	6	0	X	ET	
		5	LATCH-UP	400	6	0	X	ET	
		6	LATCH-UP	500	6	0	X	ET	

PART NUMBER:SIC645AER
LOT ID: V26V028.58
PURPOSE: QUALIFICATION

MOSFET Qualification Result

Part number/ Geometry	EBR#/LOT ID	RELIABILITY EVAL#	STRESS	Test Point	No. of Lots	No. Of Samples	Result
SIC645AER	V26V028.58	2660062	HTOL	168 Hrs	1	82	Passed
			ESD - CDM	2000 V	1	3	Passed
			ESD-HBM	4000 V	1	3	Passed
			Latch-Up	500mA @25C	1	6	Passed
				300mA at 125C	1	6	Passed
NEWG28EZPW8VS	EBR426	1966409	ESD - CDM	1000	1	10	Passed
			ESD - HBM	500 V	1	10	Passed
		1980593	RTRB	168 Hrs	1	82	Passed
			HTRB	500 Hrs	1	82	Passed
			HTGB	500 Hrs	1	82	Passed
NEWH28FZSG8VS		1966410	ESD - CDM	1000 V	1	10	Passed
			ESD - HBM	1850 V	1	10	Passed
		1980594	RTRB	168 Hrs	1	82	Passed
			HTRB	500 Hrs	1	82	Passed
			HTGB	500 Hrs	1	82	Passed